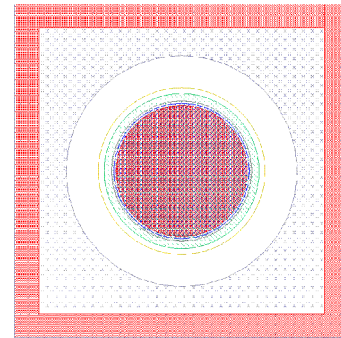


2KG028075YQ SWITCHING DIODE CHIPS**DESCRIPTION**

- 2KG028075YQ is a high speed switching diode chip fabricated in planar technology.
- This chip can be encapsulated as 1N4148 switching diode.
- When the chip is selected glass package, the chip thickness is 120 μm , and the top electrodes material is Ag bump, the back-side electrodes material is Ag.
- Chip size: 0.28 X 0.28 (mm^2).



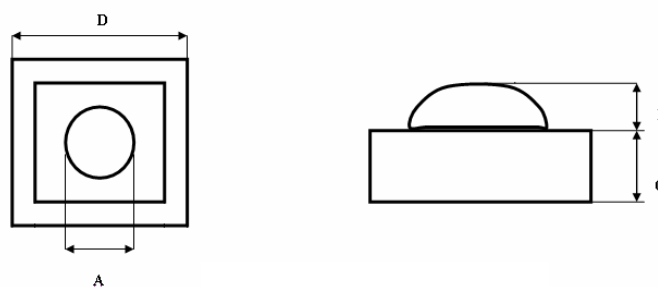
2KG028XXX CHIP TOPOGRAPHY

2KG028075YQ ELECTRICAL CHARACTERISTICS (T_J=25°C)

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	V _F	I _F =10mA.	--	--	1.0	V
		I _F =100mA.	0.62	0.9	1.2	V
Reverse voltage	V _{BR}	I _B =100 μA .	100	120	--	V
Reverse Current	I _R	V _R =20V.	--	--	25	nA
		V _R =75V.	--	--	5	μA
Diode Capacitance	C _d	f=1MHz; V _R =0.	--	1.9	4	pF
Reverse Recovery Time	t _{rr}	When switched from I _F =10mA to V _R =6V; R _L =100 Ω ; measured at I _R =1mA.	--	--	4	ns

2KG028075YQ APPEARANCE (Top side material is Ag ball)

www.DataSheet4U.com



Chip Appearance Diagram

Parameter	Symbol	Min.	Type	Max.	Unit
Chip Size	D	240	--	260	μm
Chip Thickness	C	100	--	140	μm
Bump Diameter	A	190	--	225	μm
Bump Height	B	60	80	90	μm
Scribe Line Width	/	--	40	--	μm